### Introduction to CMOS VLSI Design

#### Lecture 1: Circuits & Layout

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#### **Outline**

- □ A Brief History
- □ CMOS Gate Design
- Pass Transistors
- □ CMOS Latches & Flip-Flops
- Standard Cell Layouts
- □ Stick Diagrams

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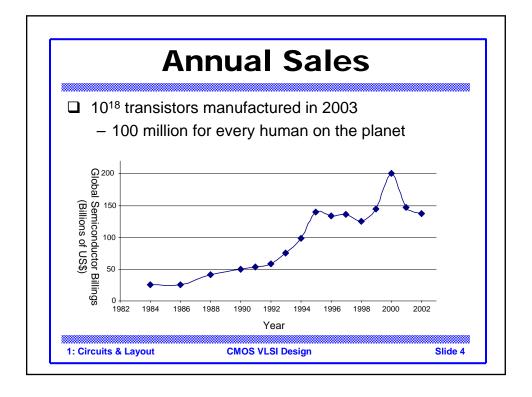
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#### **A Brief History**

- ☐ 1958: First integrated circuit
  - Flip-flop using two transistors
  - Built by Jack Kilby at Texas Instruments
- **2**003
  - Intel Pentium 4 μprocessor (55 million transistors)
  - 512 Mbit DRAM (> 0.5 billion transistors)
- □ 53% compound annual growth rate over 45 years
  - No other technology has grown so fast so long
- Driven by miniaturization of transistors
  - Smaller is cheaper, faster, lower in power!
  - Revolutionary effects on society

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#### Invention of the Transistor

- □ Vacuum tubes ruled in first half of 20<sup>th</sup> century Large, expensive, power-hungry, unreliable
- ☐ 1947: first point contact transistor
  - John Bardeen and Walter Brattain at Bell Labs
  - Read Crystal Fire
     by Riordan, Hoddeson



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#### **Transistor Types**

- Bipolar transistors
  - npn or pnp silicon structure
  - Small current into very thin base layer controls large currents between emitter and collector
  - Base currents limit integration density
- Metal Oxide Semiconductor Field Effect Transistors
  - nMOS and pMOS MOSFETS
  - Voltage applied to insulated gate controls current between source and drain
  - Low power allows very high integration

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- ☐ 1970's processes usually had only nMOS transistors
  - Inexpensive, but consume power while idle





Intel 1101 256-bit SRAM

Intel 4004 4-bit µProc

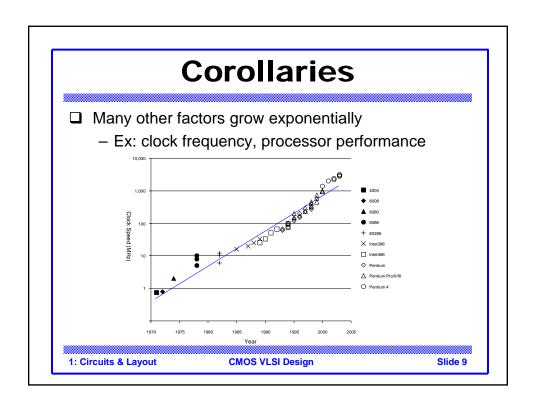
☐ 1980s-present: CMOS processes for low idle power

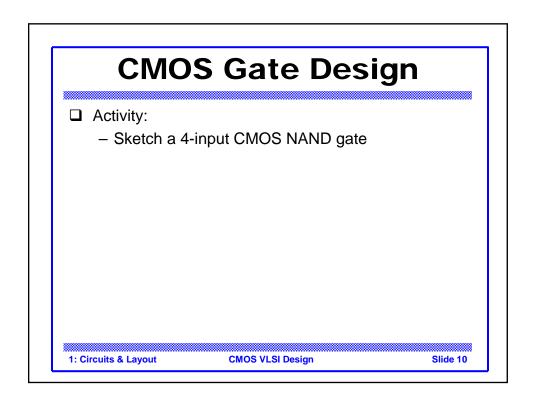
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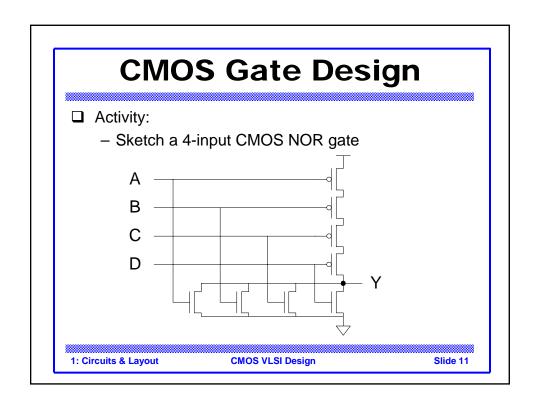
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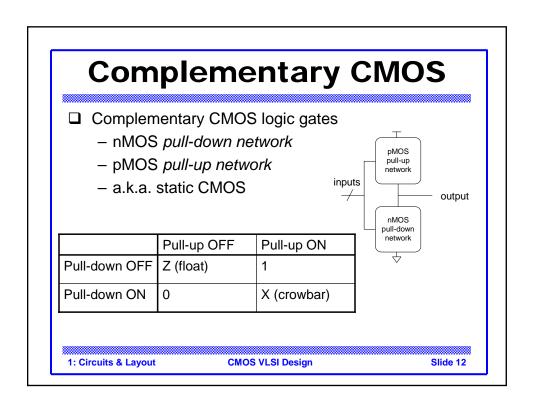
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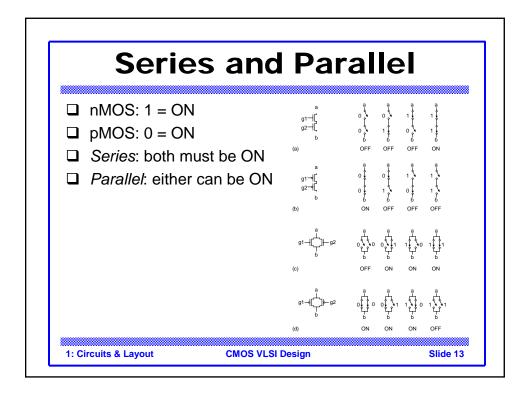
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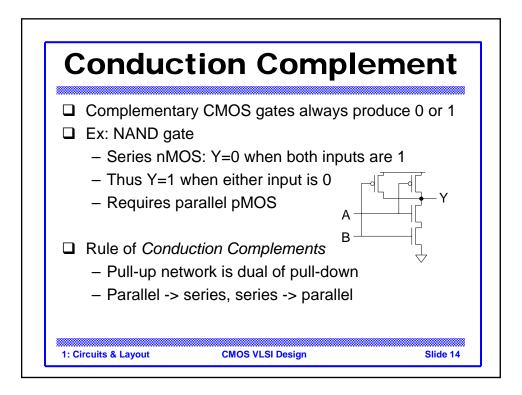


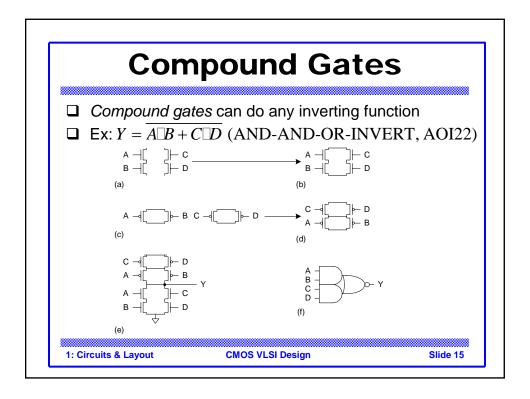








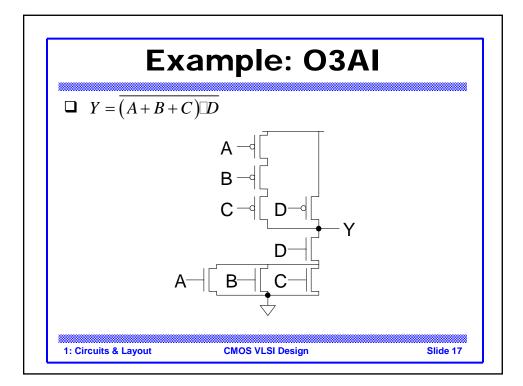




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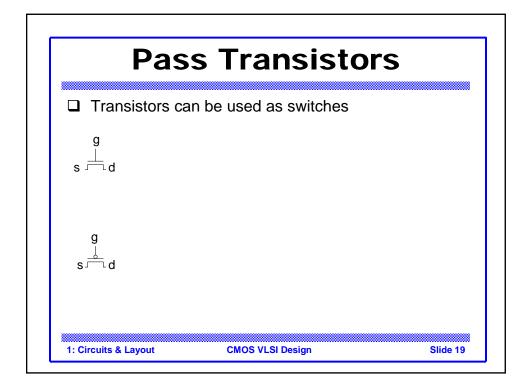


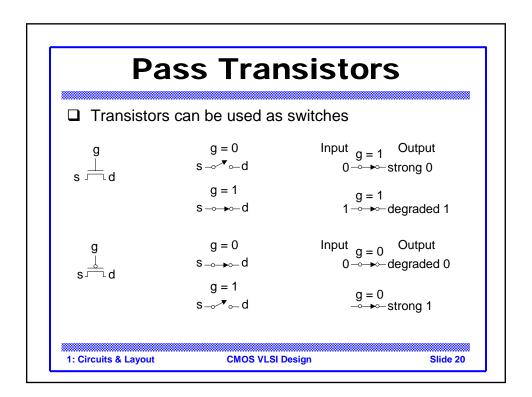
#### Signal Strength

- ☐ Strength of signal
  - How close it approximates ideal voltage source
- $\Box$   $V_{DD}$  and GND rails are strongest 1 and 0
- □ nMOS pass strong 0
  - But degraded or weak 1
- pMOS pass strong 1
  - But degraded or weak 0
- ☐ Thus nMOS are best for pull-down network

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#### **Transmission Gates**

- ☐ Pass transistors produce degraded outputs
- ☐ Transmission gates pass both 0 and 1 well

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#### **Transmission Gates**

- Pass transistors produce degraded outputs
- ☐ Transmission gates pass both 0 and 1 well

 $0 \longrightarrow -strc$  g = 1, gb = 0  $a \longrightarrow -b$  g = 1, gb = 0  $1 \longrightarrow -b$ 

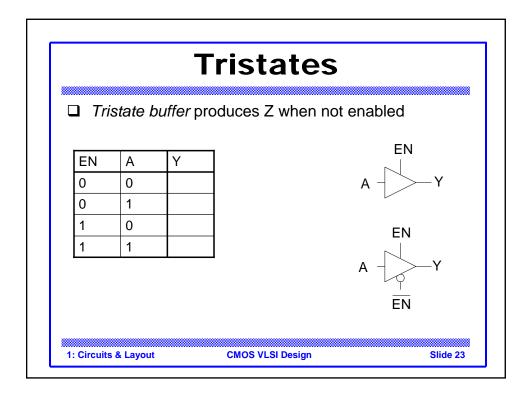
g = 0, gb = 1 g = 1, gb = 0  $0 \rightarrow \infty$  strong 0

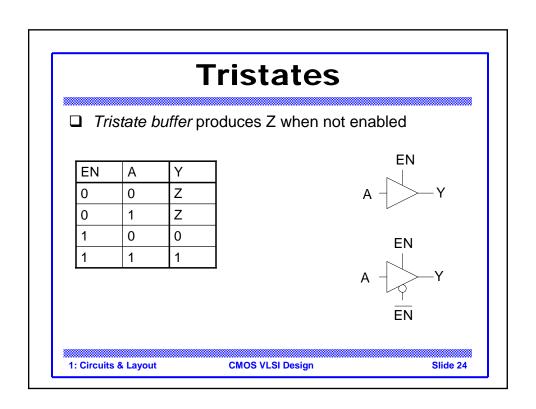
Output

1⊸→ strong 1

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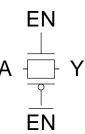
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#### **Nonrestoring Tristate**

- ☐ Transmission gate acts as tristate buffer
  - Only two transistors
  - But nonrestoring
    - Noise on A is passed on to Y



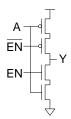
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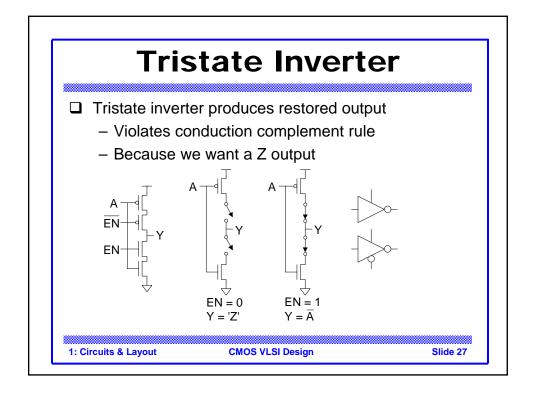
#### **Tristate Inverter**

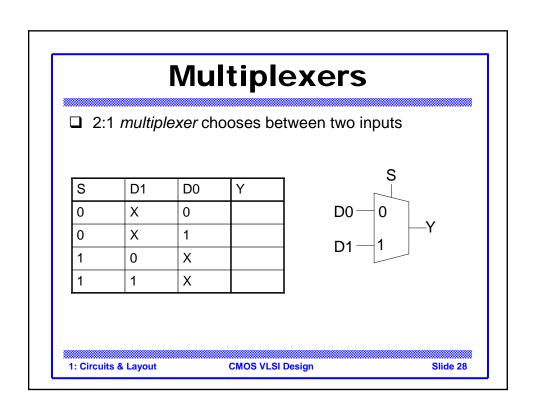
- ☐ Tristate inverter produces restored output
  - Violates conduction complement rule
  - Because we want a Z output

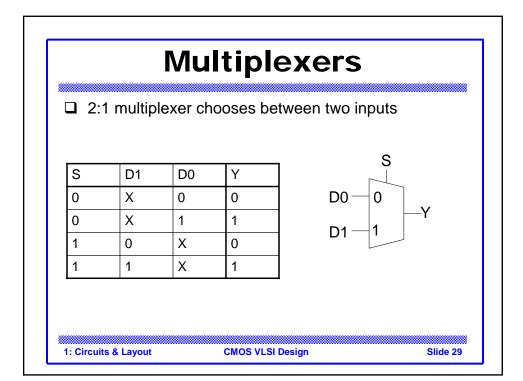


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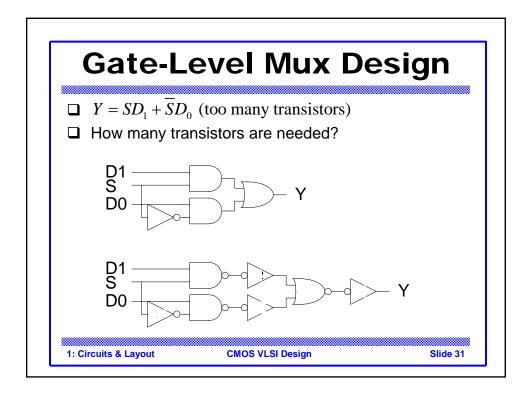
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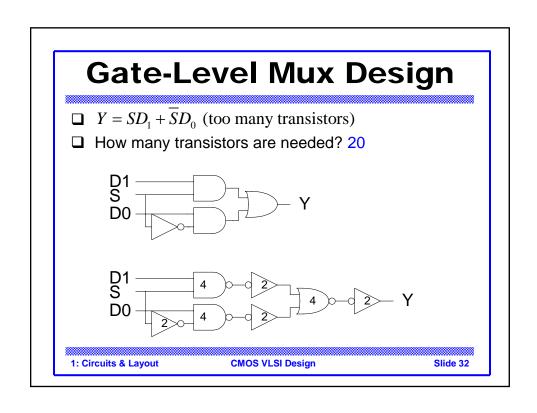






# Gate-Level Mux Design $Y = SD_1 + \overline{S}D_0 \text{ (too many transistors)}$ How many transistors are needed?

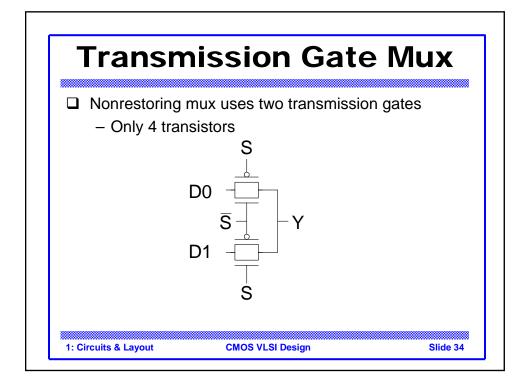




# Transmission Gate Mux ☐ Nonrestoring mux uses two transmission gates

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#### 4:1 Multiplexer

☐ 4:1 mux chooses one of 4 inputs using two selects

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